

S102S01/S102S02 S202S01 /s202s02

SIP Type **SSR** for Medium Power Control

■ Features

1. High radiation resin mold package
2. RMS ON-state current
 I_T : 8 Arms at $T_c \leq 80^\circ\text{C}$
(With heat sink)
3. Built-in zero-cross circuit
(s102s02/s202s02)
4. High repetitive peak OFF-state voltage
S102SO1/S102S02 V_{DRM} : MIN. 400V
S202S01 /S202S02 V_{DRM} : MIN. 600V
5. Isolation voltage between input and output
(V_{iso} : 4000Vrms)
6. Approved by CSA, No, LR63705
Recognized by UL, file No. E94758

■ Applications

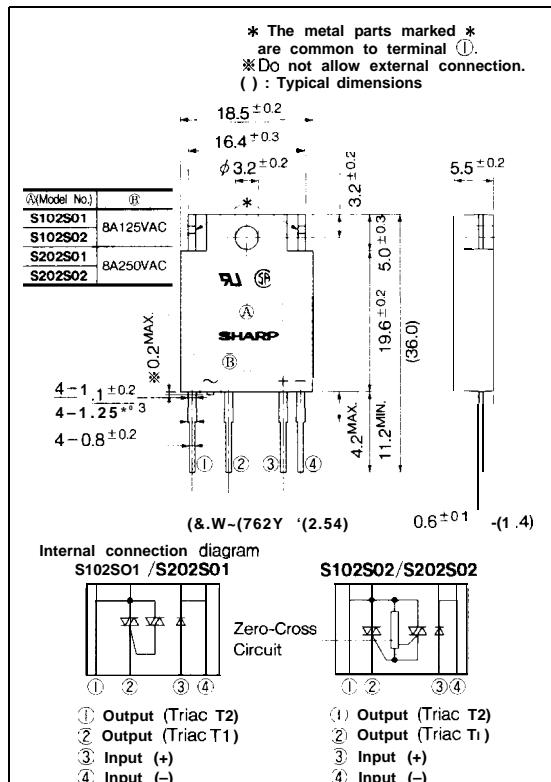
1. Automatic vending machines, programmable controllers
2. Amusement equipment

■ Model Line-ups

	For 100V lines	For 200V lines
For phase control		
No built-in zero-cross circuit	S102S01	S202S01
Built in zero cross circuit	S102S02	S202S02

■ Outline Dimensions

(Unit : mm)



■ Absolute Maximum Ratings

(Ta = 25°C)

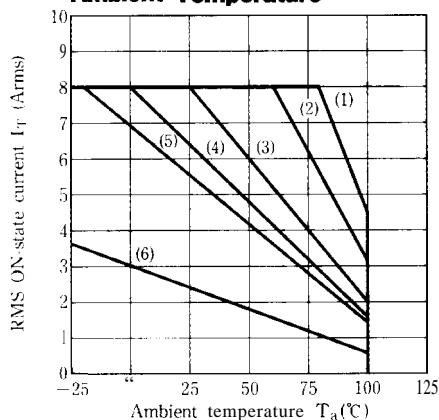
Parameter		Symbol	Rating		Unit	*1 T' $\leq 80^\circ\text{C}$ *2 50Hz sine wave, T _j = 25°C start *360Hz AC for 1 minute, 40 min 60%RH, Apply voltages between input and output, by the dielectric withstand voltage tester with zero- cross circuit. (Input and output shall be shorted respectively). (Note)	
			S102S01 S102S02	S202S01 S202S02			
Input	Forward current	I _F	50	mA	*		
	Reverse voltage	V _R	6	v			
output	*1 RMS ON-state current	I _T	8	A _{rms}			
	*2 Peak one cycle surge current	I _{surge}	80	A			
	Repetitive peak OFF-state voltage	V _{DRM}	400	600	v		
	Non-repetitive peak OFF-state voltage	V _{DSM}	400	600	V		
	Critical rate of rise of ON state current	dI/dt	50		A/ μs		
	Operating frequency	f	45 to 65		Hz		
*3 Isolation voltage	V _{iso}	4000		v _{rms}			
Operating temperature	T _{opr}	-25 to +100		°c			
Storage temperature	T _{stg}	-30 to +125		°c			
*4 Soldering temperature	T _{sol}	260		°c			

■ Electro-optical Characteristics

(Ta = 25°C)

Parameter		Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Input	Forward voltage	V _F	I _F = 20mA		1.2	1.4	V
	Reverse current	I _R	V _R = 3V	—	—	10 ⁻⁴	A
Output	Repetitive peak OFF-state current	I _{DRM}	V _D = V _{DRM}		—	10 ⁴	A
	ON-state voltage	V _T	Resistance load I _F = 20mA, I _L = 2A, t = 1ms		—	1.5	V _{rms}
	Holding current	I _H				50	mA
	Critical rate of rise of OFF-state voltage	dV/dt	V _D = 2/3 . V _{DRM}	30		—	V/μs
Transfer characteristics	Critical rate of rise of commutating OFF-state voltage	(dV/dt) _C	T _j = 125°C, dI _T /dt = -4.0A/ms, V _D = 400V	5		—	V/μs
	Zero-cross voltage	V _{Ox}	I _F = 8mA			35	V
	Minimum trigger current	I _{FT}	V _D = 12V, R _L = 30Ω	—	—	8	mA
			V _D = 6V, R _L = 30Ω			8	mA
Isolation resistance	Isolation resistance	R _{ISO}	DC500V, 40 to 60%RH	10 ¹⁰		—	Ω
	Turn-on time	t _{on}	AC 50Hz	—	—	1	ms
	Turn-off time	t _{off}		—	—	10	ms
Thermal resistance (Between junction and case)		R _{th(j-c)}			4.5	—	°C/W
Thermal resistance (Between junction and ambience)		R _{th(j-a)}			40	—	°C/W

Fig. 1 RMS ON-state Current vs.
Ambient Temperature



- (1) With infinite heat sink
- (2) With heat sink (200 × 200 × 2mm Al plate)
- (3) With heat sink (100 × 100 × 2mm Al plate)
- (4) With heat sink (75 × 75 × 2mm Al plate)
- (5) With heat sink (50 × 50 × 2mm Al plate)
- (6) Without heat sink

(Note) With the Al heat sink set up vertically, tighten the device at the center of the Al heat sink with a torque of 0.4N m and apply thermal conductive silicone grease on the heat sink mounting plate. Forcible cooling shall not be carried out.

Fig. 2 RMS ON-state Current vs. Case Temperature

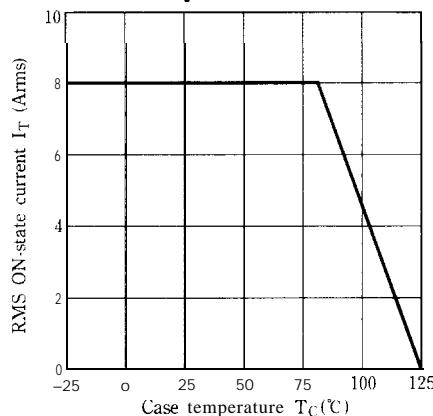
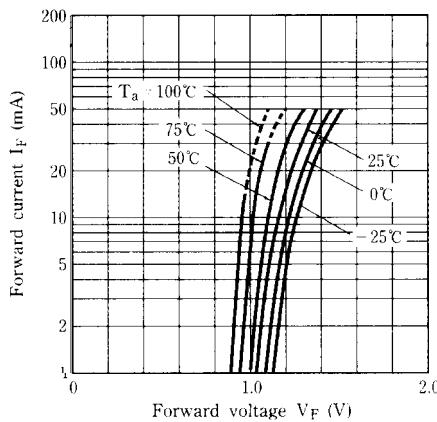


Fig. 4 Forward Current vs. Forward Voltage



6 Maximum ON-state Power Dissipation vs. RMS ON-state Current

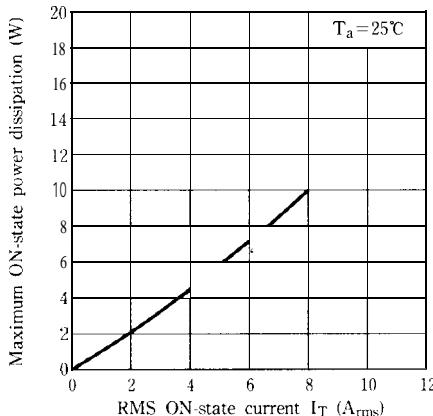


Fig. 3 Forward Current vs. Ambient Temperature

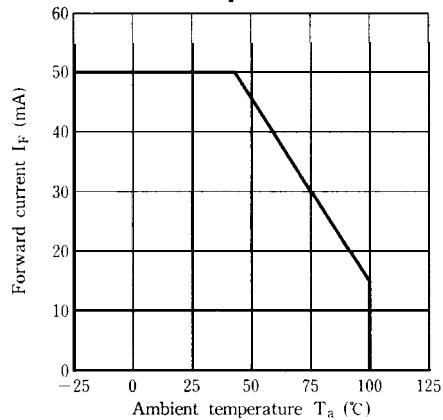


Fig. 5 Surge Current vs. Power-on Cycle

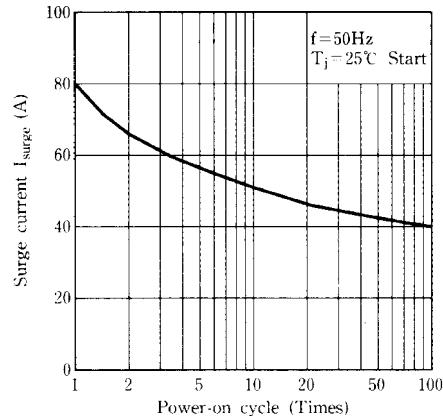


Fig. 7 Minimum Trigger Current vs. Ambient Temperature

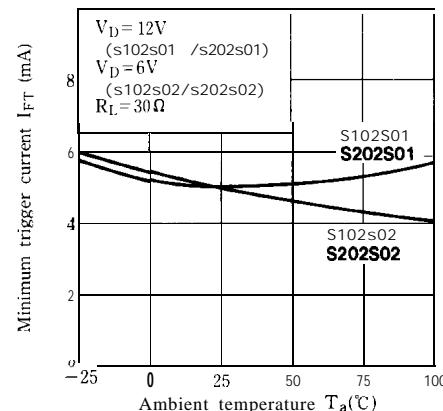


Fig. 8 Relative Repetitive Peak OFF-state Voltage vs. Ambient Temperature

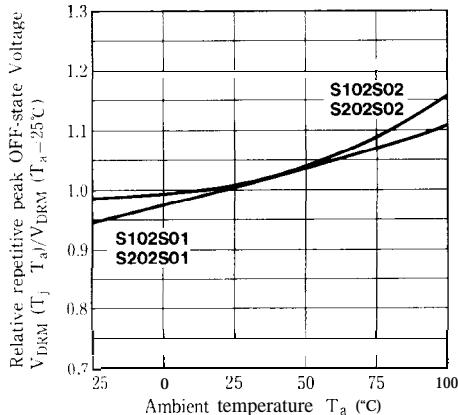
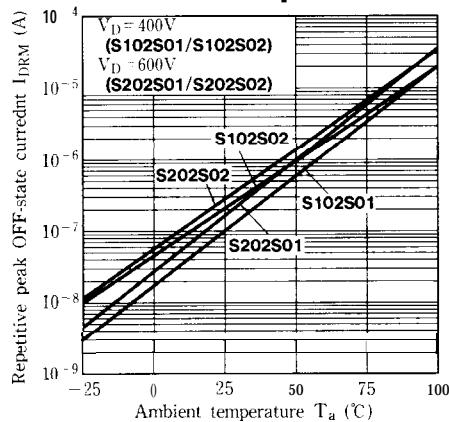


Fig. 9 Repetitive Peak OFF-state Current vs. Ambient Temperature



- Please refer to the chapter "Precautions for Use" (Page 78 to 93).